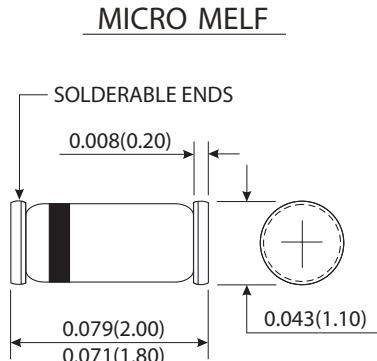


Features

- Silicon epitaxial planar diode
- Fast switching diodes
- 500mW power dissipation
- This diode is also available in the DO-35 case with the type designation 1N4148

Mechanical Data

- Case: Mini-MELF glass case(DO-35)
- Weight: Approx. 0.05 gram



Dimensions in inches and (millimeters)

Maximum Ratings And Electrical Characteristics

(Ratings at 25 °C ambient temperature unless otherwise specified)

| | Symbol | Value | Units |
|---|------------------|-------------------|-------|
| Reverse Voltage | VR | 75 | Volts |
| Peak Reverse Voltage | V _{RM} | 100 | Volts |
| Average rectified current, Half wave rectification with Resistive load at TA=25 °C and F ≥ 50Hz | I _{AV} | 150 ¹⁾ | mA |
| Surge forward current at t<1S and TJ=25 °C | I _{FSM} | 500 | mA |
| Power dissipation at TA=25 °C | P _{tot} | 500 ¹⁾ | mW |
| Junction temperature | T _J | 175 | °C |
| Storage temperature range | T _{STG} | -65 to +175 | °C |

1) Valid provided that leads at a distance of 8mm from case are kept at ambient temperature(DO-35)

Electrical characteristics

(Ratings at 25 °C ambient temperature unless otherwise specified)

| | Symbols | Min. | Typ. | Max. | Units |
|--|-------------------|------|------|-------------------|-------|
| Forward voltage | V _F | | | 1 | Volts |
| Leakage current at VR=20V | I _R | | | 25 | nA |
| at VR=75V | I _R | | | 5 | µA |
| at VR=20V, TJ=150 °C | I _R | | | 50 | µA |
| Junction Capacitance at VR=VF=0V | C _J | | | 4 | pF |
| Voltage rise when switching ON tested with 50mA pulse tp=0.1 µS, Rise time<30 µS, fp=5 to 100KHz | V _f r | | | 2.5 | Volts |
| Reverse Recovery time from I _F =10mA to I _R =1mA, VR=6V, RL=100 Ω | t _{rr} | | | 4 | ns |
| Thermal resistance, junction to Ambient | R _{θ JA} | | | 350 ¹⁾ | K/W |
| Rectification efficiency at f=100MHz, V _{RF} =2V | η | 0.45 | | | |

1) Valid provided that leads at a distance of 8mm from case are kept at ambient temperature(DO-35)

DEC

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FIG.1-FORWARD CHARACTERISTICS

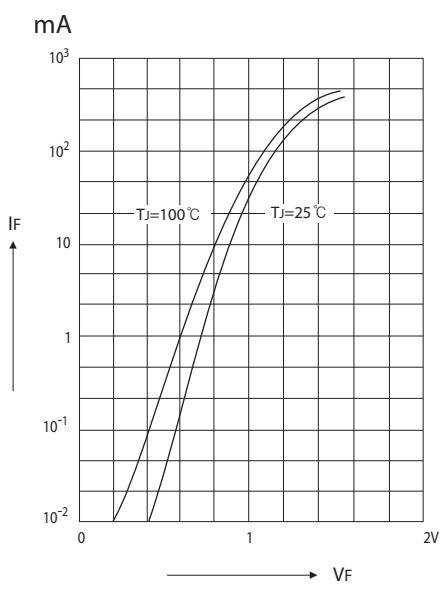


FIG.2-DYNAMIC FORWARD RESISTANCE
VERSUS FORWARD CURRENT

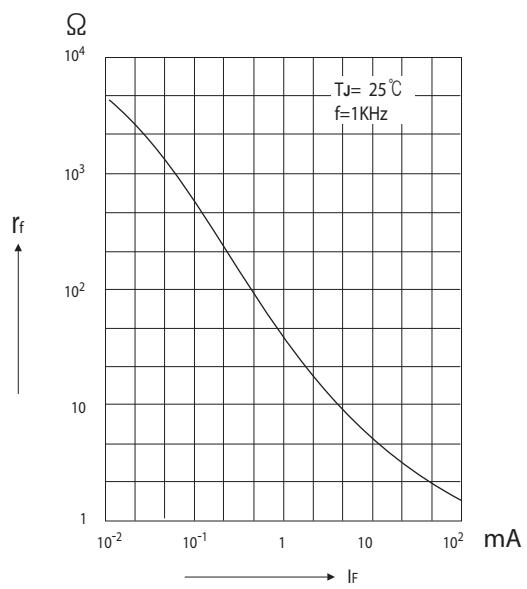


FIG.3-ADMISSIBLE POWER DISSIPATION
VERSUS AMBIENT TEMPERATURE

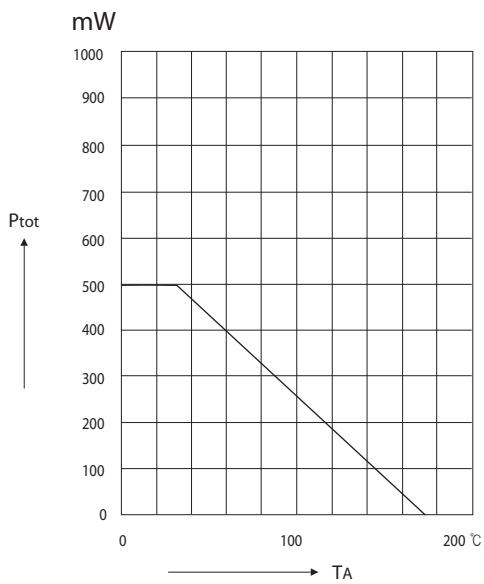
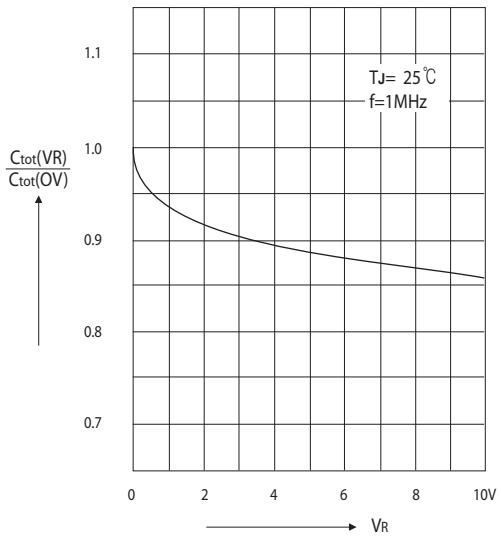


FIG.4-RELATIVE CAPACITANCE VERSUS
VOLTAGE



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FIG.5-RECTIFICATION EFFICIENCY MEASUREMENT CIRCUIT

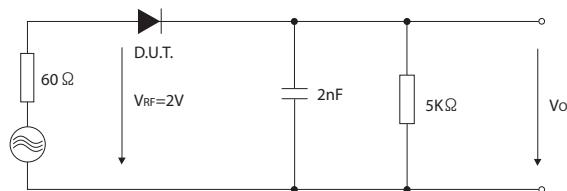


FIG.6-LEAKAGE CURRENT VERSUS JUNCTION TEMPERATURE

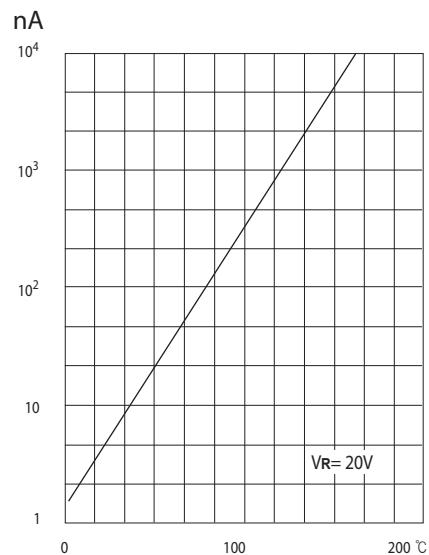


FIG.7-ADMISSIBLE REPETITIVE PEAK FORWARD CURRENT VERSUS PULSE DURATION

